PNP/NPN Epitaxial Planar Silicon Transistors



2SB922L/2SD1238L

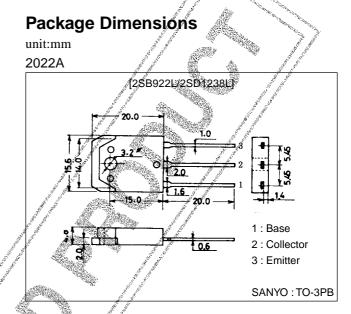
80V/12A Switching Applications

Applications

• Suittable for relay drivers, high-speed inverters, converters, and other large-current switching applications.

Features

- · Low collector-to-emitter saturation voltage : $V_{CE(sat)}$ =-0.5V (PNP), 0.4V (NPN) max.
- Wide ASO and highly resistant to breakdown.



():2SB922L

Specifications

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol Symbol	Ratings	Unit
Collector-to-Base Voltage	VCB0	(–)90	V
Collector-to-Emitter Voltage	VGEO	(–)80	V
Emitter-to-Base Voltage	N _{EBO}	(–)6	V
Collector Current		(–)12	A
Collector Current (Pulse)	I _{CP}	(–)20	A
Collector Dissipation	P _C Tc=25 C	80	W
Junction Temperature		150	°C
Storage Temperature	a tstg	-55 to +150	°C

Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Onit
Collector Cutoff Current	СВО	V _{CB} =(–)80V, I _E =0			(–)0.1	mA
Emitter Cutoff Current	IEBO /	V _{EB} =(-)4V, I _C =0			(–)0.1	mA
DC Current Gain	h _F Ę1	V _{CE} =(-)2V, I _C =(-)1A	70*		280*	
DC Current Gain	h∉Ę2	V _{CE} =(-)2V, I _C =(-)6A	30			
Gain-Bandwidth Broduct	۶Ť	V _{CE} =(-)5V, I _C =(-)1A		20		MHz
Collector-to-Emitter Saturation Voltage	VCE(sat)	I _C =(-)6A, I _B =(-)0.6A			0.4	V
					(-0.5)	V

\ast : The 2SB992L/2SD1238L are classified by 1A h_{FE} as follows :

70 Q 140 100 R 200 140 S 280

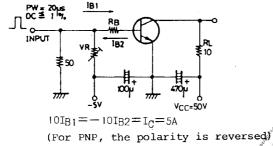
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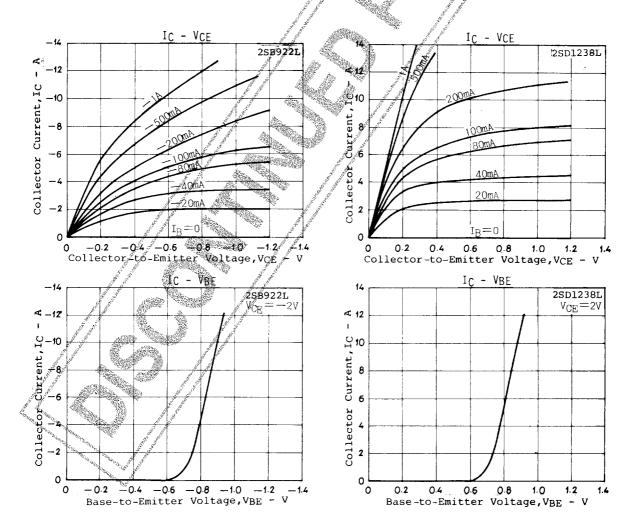
SANYO Electric Co., Ltd. Semiconductor Bussiness Headquaters TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

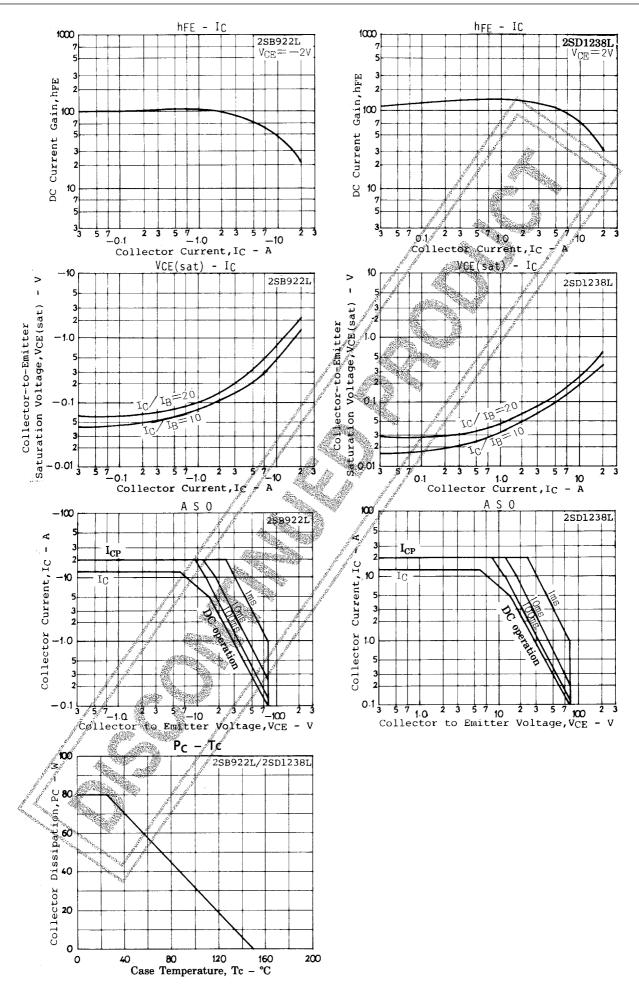
Parameter	Symbol	Conditions		Ratings		
			min	typ	max	Unit
Collector-to-Base Breakdown Voltage	V _(BR) CBO	I _C =(-)1mA, I _E =0	(–)90			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	I _C =(−)1mA, R _{BE} =∞	(–)80			V
Emitter-to-Base Breakdown Voltage	V(BR)EBO	I _E =(-)1mA I _C =0	(–)6			V
Turn-ON Time	ton	See specified Test Circuit	all the second sec	0.2		μs
Storage Time	tstg	See specified Test Circuit	And and a second second	(0.7)		μs
			J. C.	4,7	CEAL SOL	μs
Fall Time	t _f	See specified Test Circuit	and the second second	(0.1)	State of the second state	μs
				0.2	No. of Concession, State	ys

Switching Time Test Circuit



Unit (resistance : Ω , capacitance : F)





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